

P-Channel Enhancement-Mode Power Field-Effect Transistors

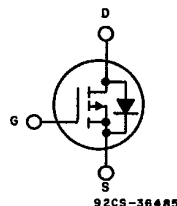
10 A, -120V and -150 V

 $r_{DS(on)} = 0.5 \Omega$

Features:

- SOA is power-dissipation limited
- Nanosecond switching speeds
- Linear transfer characteristics
- High input impedance
- Majority carrier device

TERMINAL DIAGRAM



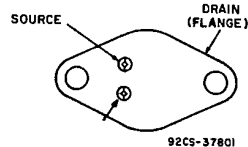
P-CHANNEL ENHANCEMENT MODE

The RFM10P12 and RFM10P15 and the RFP10P12 and RFP10P15* are p-channel enhancement-mode silicon-gate power field-effect transistors designed for applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high-power bipolar switching transistors requiring high speed and low gate-drive power. These types can be operated directly from integrated circuits.

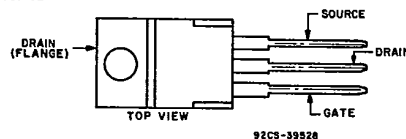
The RFM-types are supplied in the JEDEC TO-204AA steel package and the RFP-types in the JEDEC TO-220AB plastic package.

*The RFM and RFP series were formerly RCA developmental TA9404 and TA9405, respectively.

TERMINAL DESIGNATIONS

RFM10P12
RFM10P15

JEDEC TO-204AA

RFP10P12
RFP10P15

JEDEC TO-220AB

MAXIMUM RATINGS, Absolute-Maximum Values ($T_C = 25^\circ\text{C}$):

	RFM10P12	RFM10P15	RFP10P12	RFP10P15		
DRAIN-SOURCE VOLTAGE	V_{DS}	-120	-150	-120	-150	V
DRAIN-GATE VOLTAGE ($R_{DS} = 1 \text{ M}\Omega$)	V_{DGR}	-120	-150	-120	-150	V
GATE-SOURCE VOLTAGE	V_{GS}	± 20				V
DRAIN CURRENT, RMS Continuous	I_D	10				A
Pulsed	I_{DM}	30				A
POWER DISSIPATION @ $T_C = 25^\circ\text{C}$	P_T	100	100	75	75	W
Derate above $T_C = 25^\circ\text{C}$	-	0.8	0.8	0.6	0.8	W/ $^\circ\text{C}$
OPERATING AND STORAGE TEMPERATURE	T_J, T_{stg}	-55 to +150				$^\circ\text{C}$

RFM10P12, RFM10P15, RFP10P12, RFP10P15

ELECTRICAL CHARACTERISTICS, At Case Temperature ($T_c = 25^\circ\text{C}$) unless otherwise specified

T-39-23

CHARACTERISTIC	SYMBOL	TEST CONDITIONS	LIMITS				UNITS
			RFM10P12 RFP10P12		RFM10P15 RFP10P15		
			MIN.	MAX.	MIN.	MAX.	
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D = 1\text{ mA}$ $V_{GS} = 0$	-120	—	-150	—	V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}$ $I_D = 1\text{ mA}$	-2	-4	-2	-4	V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -100\text{ V}$	—	1	—	—	μA
		$V_{DS} = -120\text{ V}$	—	—	—	1	
		$T_C = 125^\circ\text{C}$ $V_{DS} = -100\text{ V}$	—	50	—	—	
		$V_{DS} = -120\text{ V}$	—	—	—	50	
Gate-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{ V}$ $V_{DS} = 0$	—	100	—	100	nA
Drain-Source On Voltage	$V_{DS(on)}^a$	$I_D = 5\text{ A}$ $V_{GS} = -10\text{ V}$	—	-2.5	—	-2.5	V
		$I_D = 10\text{ A}$ $V_{GS} = -10\text{ V}$	—	-6.0	—	-6.0	
Static Drain-Source On Resistance	$r_{DS(on)}^a$	$I_D = 5\text{ A}$ $V_{GS} = -10\text{ V}$	—	0.5	—	0.5	Ω
Forward Transconductance	g_{fs}^a	$V_{DS} = -10\text{ V}$ $I_D = 5\text{ A}$	2	—	2	—	mho
Input Capacitance	C_{iss}	$V_{DS} = -25\text{ V}$	—	1700	—	1700	pF
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}$	—	600	—	600	
Reverse Transfer Capacitance	C_{rss}	$f = 1\text{ MHz}$	—	150	—	150	
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = -75\text{ V}$	24(typ)	50	24(typ)	50	ns
Rise Time	t_r	$I_D = 5\text{ A}$	74(typ)	150	74(typ)	150	
Turn-Off Delay Time	$t_{d(off)}$	$R_{gen} = R_{gs} = 50\ \Omega$	138(typ)	225	138(typ)	225	
Fall Time	t_f	$V_{GS} = -10\text{ V}$	61(typ)	100	61(typ)	100	
Thermal Resistance Junction-to-Case	$R\theta_{JC}$	RFM10P12, RFM10P15	—	1.25	—	1.25	$^\circ\text{C/W}$
		RFP10P12, RFP10P15	—	1.67	—	1.67	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITIONS	LIMITS				UNITS
			RFM10P12 RFP10P12		RFM10P15 RFP10P15		
			MIN.	MAX.	MIN.	MAX.	
Diode Forward Voltage	V_{SD}^a	$I_{SD} = 5A$	—	1.4	—	1.4	V
Reverse Recovery Time	t_{rr}	$I_F = 4A, dI_F/dt = 100A/\mu s$	210 (typ.)		210 (typ.)		ns

^a Pulsed: Pulse duration = 300 μs max., duty cycle = 2%.

Standard Power MOSFETs

RFM10P12, RFM10P15, RFP10P12, RFP10P15

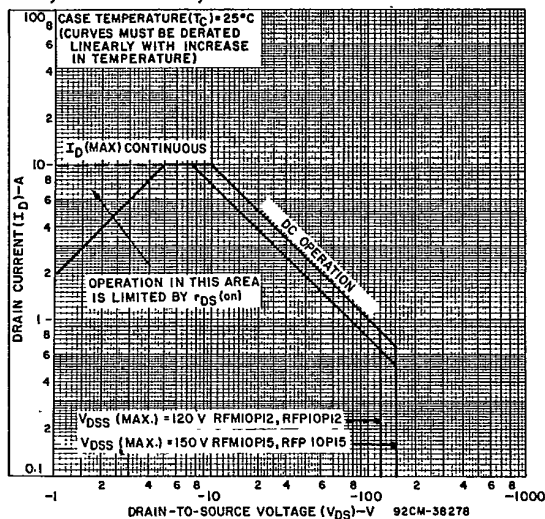


Fig. 1 - Maximum safe operating areas for all types.

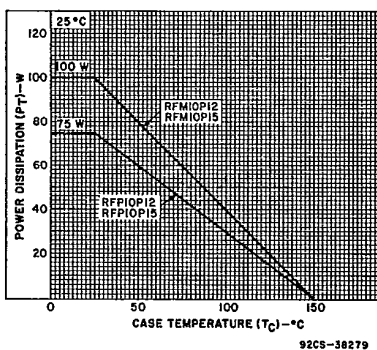


Fig. 2 - Power dissipation vs. case temperature derating curve for all types.

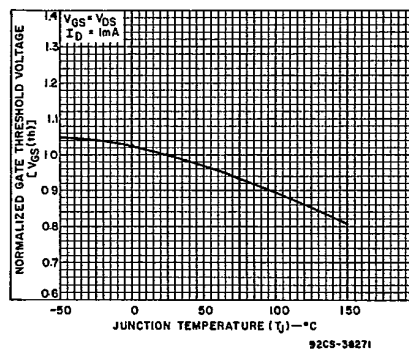


Fig. 3 - Typical normalized gate threshold voltage as a function of junction temperature for all types.

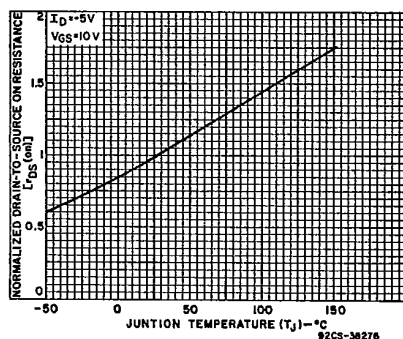


Fig. 4 - Normalized drain-to-source on resistance as a function of junction temperature for all types.

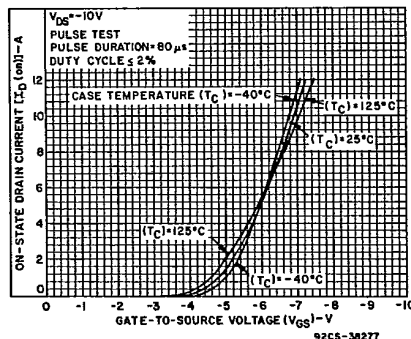


Fig. 5 - Typical transfer characteristics for all types.

RFM10P12, RFM10P15, RFP10P12, RFP10P15

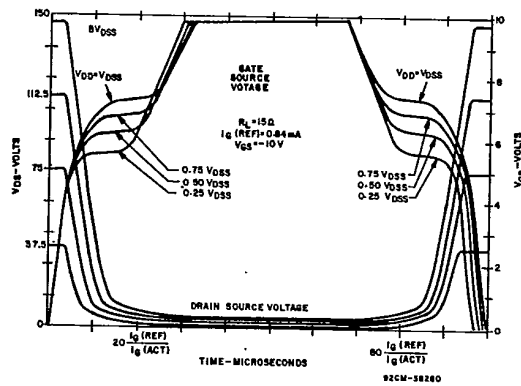


Fig. 6 - Normalized switching waveforms for constant gate-current drive. Refer to RCA Power MOSFETs PMP411A.

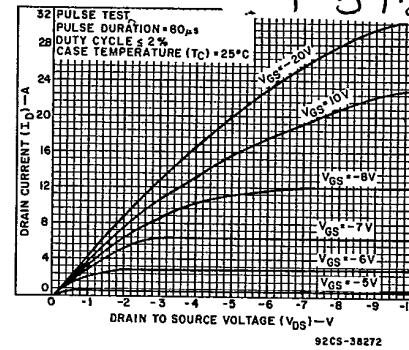


Fig. 7 - Typical saturation characteristics for all types.

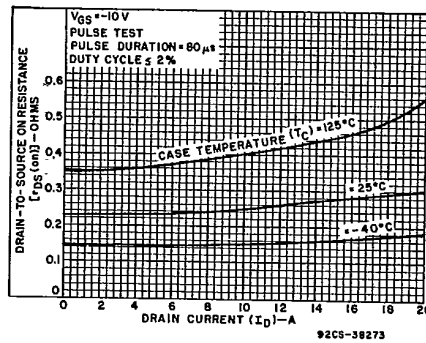


Fig. 8 - Typical drain-to-source on resistance as a function of drain current for all types.

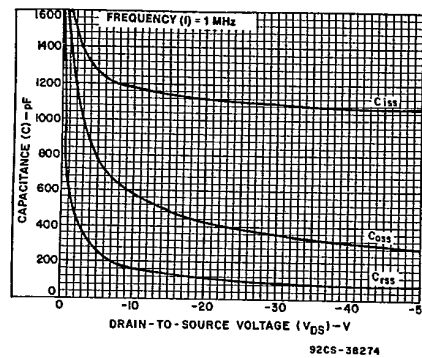


Fig. 9 - Capacitance as a function of drain-to-source voltage for all types.

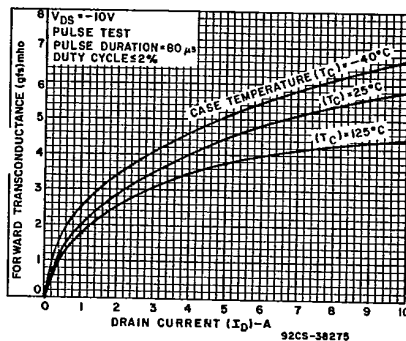


Fig. 10 - Typical forward transconductance as a function of drain current for all types.

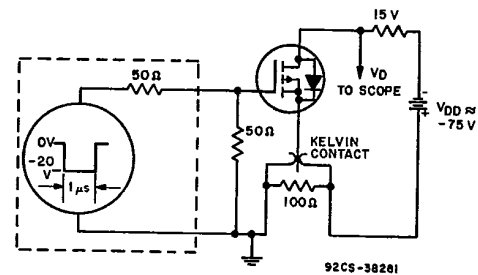


Fig. 11 - Switching Time Test Circuit.